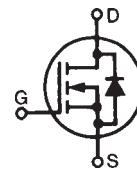
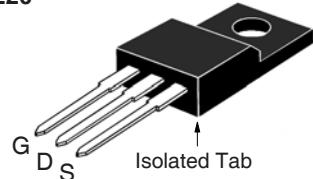


**X-Class HiPERFET
Power MOSFET**
IXFP8N85XM
(Electrically Isolated Tab)

N-Channel Enhancement Mode
 $V_{DSS} = 850V$
 $I_{D25} = 8A$
 $R_{DS(on)} \leq 850m\Omega$
**OVERMOLDED
TO-220**

G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	850	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	850	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$, Limited by T_{JM}	8	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	16	A
I_A	$T_C = 25^\circ C$	4	A
E_{AS}	$T_C = 25^\circ C$	300	mJ
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	50	V/ns
P_D	$T_C = 25^\circ C$	33	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
V_{ISOL}	50/60 Hz, 1 Minute	2500	V \sim
M_d	Mounting Torque	1.13 / 10	Nm/lb.in
Weight		2.5	g

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	850		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	3.0		V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			$10 \mu A$ $750 \mu A$
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 4A$, Note 1			850 m Ω

Features

- International Standard Package
- Plastic Overmolded Tab
- High Voltage Package
- Low $R_{DS(on)}$ and Q_G
- Avalanche Rated
- 2500V~ Electrical Isolation
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

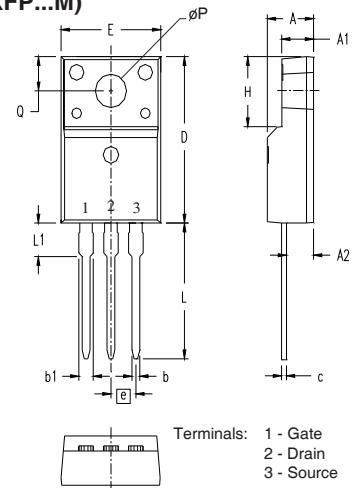
Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	V _{DS} = 10V, I _D = 4A, Note 1	2.7	4.5	S
R_{Gi}	Gate Input Resistance		3	Ω
C_{iss} C_{oss} C_{rss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	654 714 11		pF
Effective Output Capacitance				
C_{o(er)} C_{o(tr)}	Energy related } V _{GS} = 0V Time related } V _{DS} = 0.8 • V _{DSS}	40 120		pF
Q_{g(on)} Q_{gs} Q_{gd}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 4A	17.0 3.6 10.0		nC
t_{d(on)} t_r t_{d(off)} t_f	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 4A R _G = 10Ω (External)	15 25 32 23		ns
R_{thJC} R_{thCS}		0.50	3.78 °C/W °C/W	

Source-Drain Diode

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I _s	V _{GS} = 0V		8	A
I _{SM}	Repetitive, pulse Width Limited by T _{JM}		32	A
V _{SD}	I _F = I _S , V _{GS} = 0V, Note 1		1.4	V
t_{rr} Q_{RM} I_{RM}	I _F = 4A, -di/dt = 100A/μs V _R = 100V	125 1.1 18.0		ns μC A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

OVERMOLDED TO-220 (IXFP...M)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 5,017,508 5,063,307 5,381,025 6,259,123B1 6,534,343 6,710,405B2 6,759,692 7,063,975B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728B1 6,583,505 6,710,463 6,771,478B2 7,005,734B2 7,157,338B2

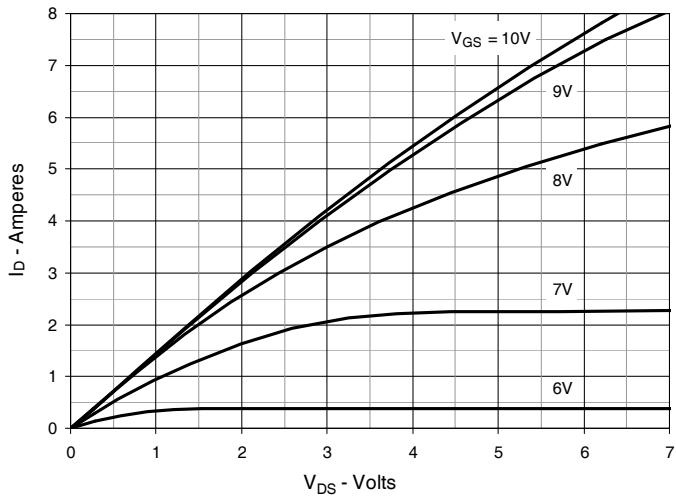
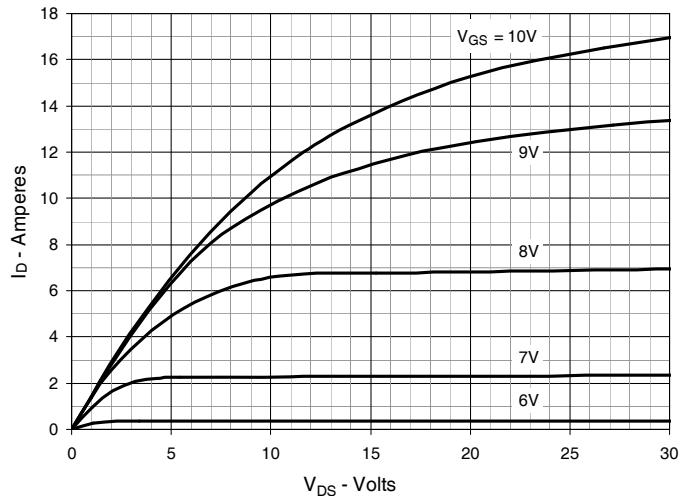
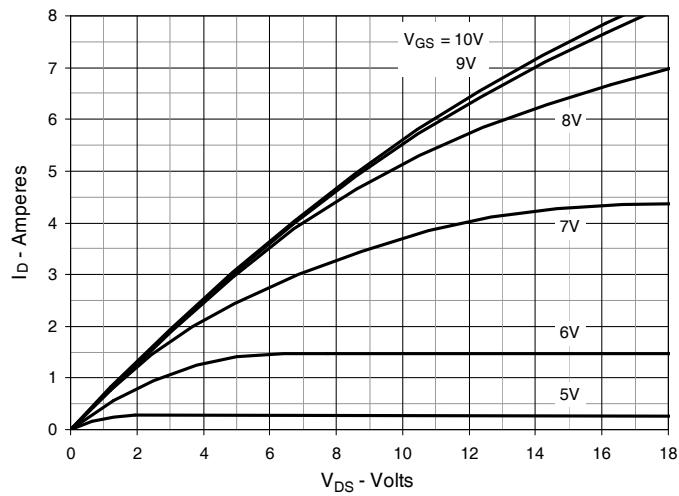
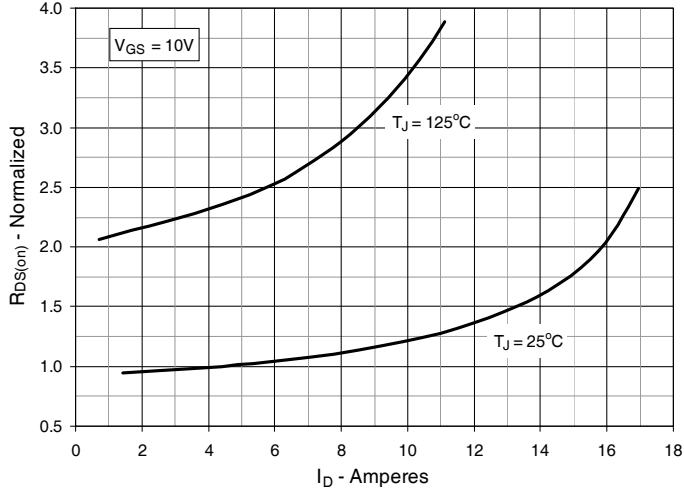
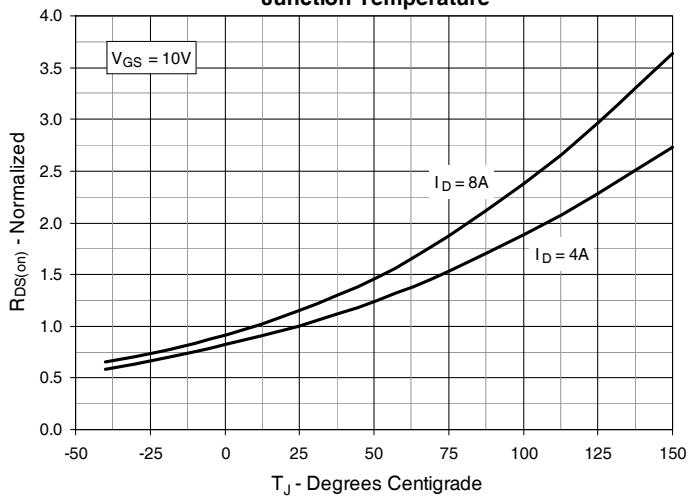
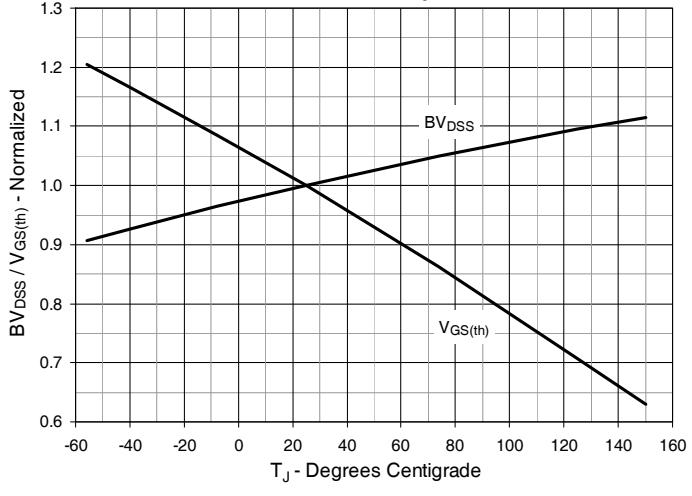
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ **Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$** **Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$** **Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 4A$ Value vs. Drain Current****Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 4A$ Value vs. Junction Temperature****Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**

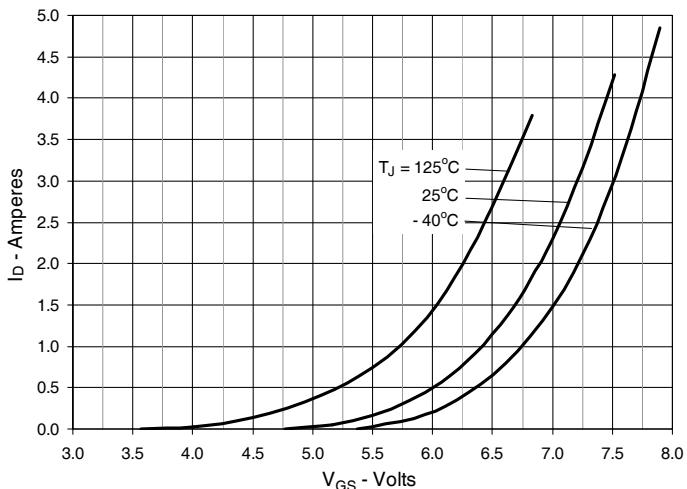
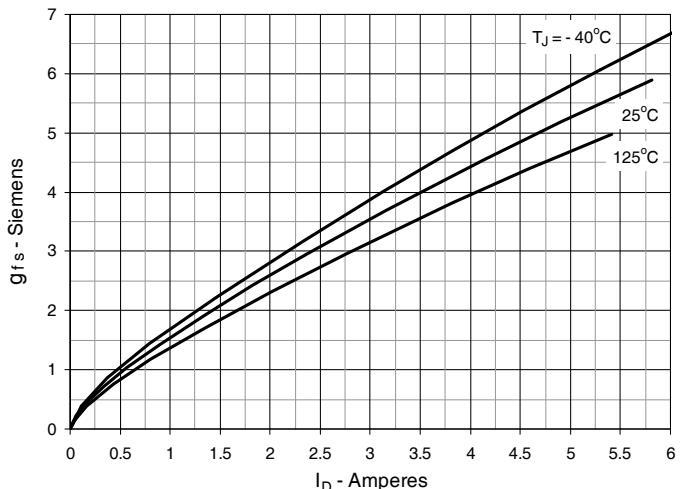
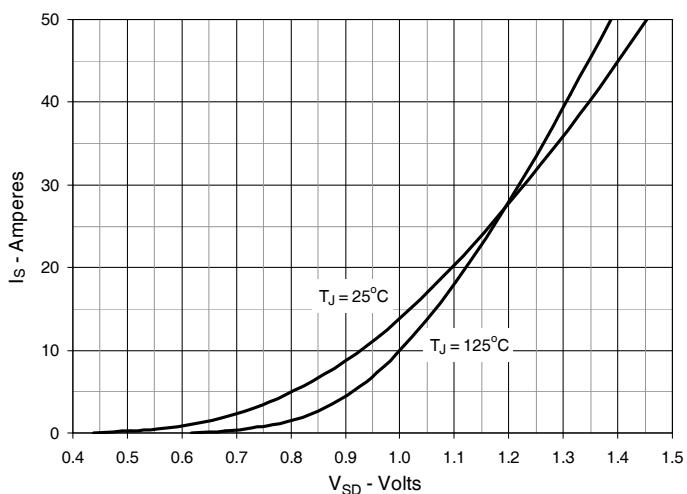
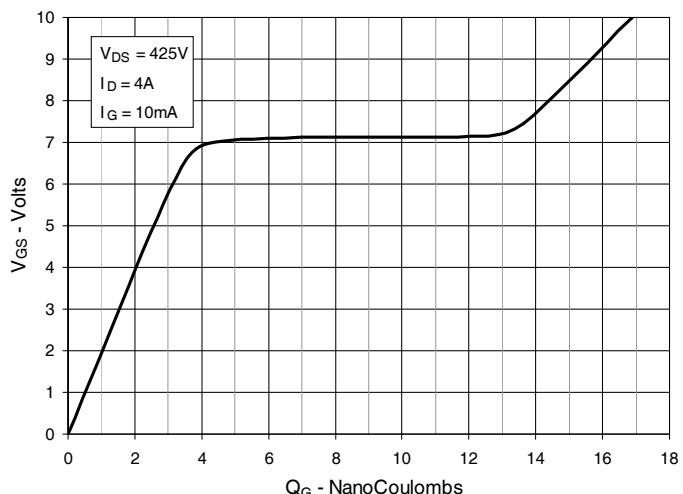
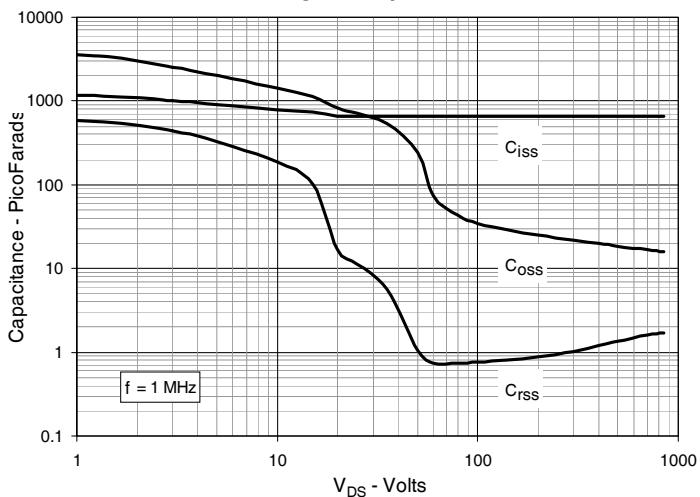
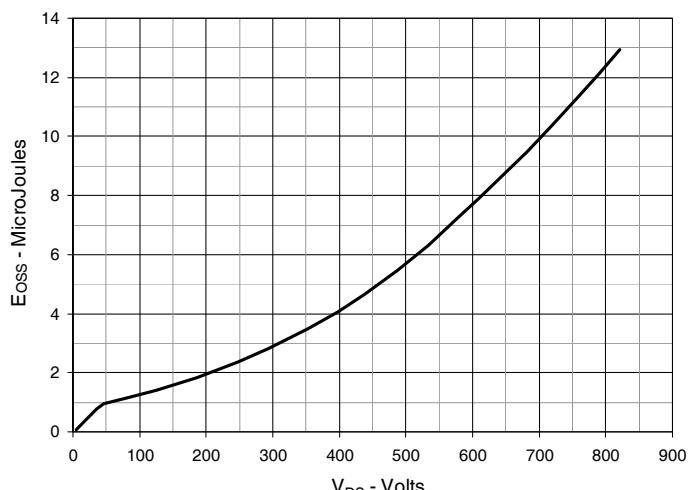
Fig. 7. Input Admittance**Fig. 8. Transconductance****Fig. 9. Forward Voltage Drop of Intrinsic Diode****Fig. 10. Gate Charge****Fig. 11. Capacitance****Fig. 12. Output Capacitance Stored Energy**

Fig. 13. Forward-Bias Safe Operating Area

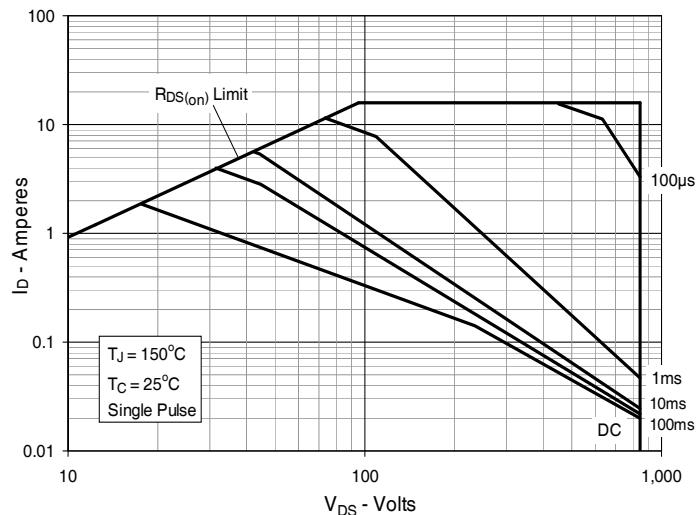
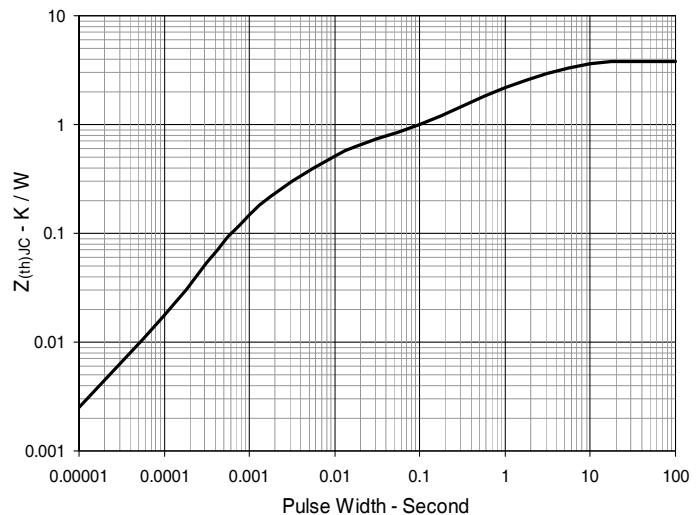


Fig. 14. Maximum Transient Thermal Impedance



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